



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

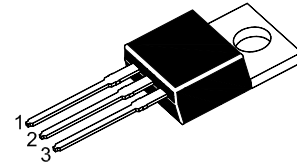
TEL: 852-2790 0314 FAX: 852-2790 0206

ST 13003

NPN Silicon Epitaxial Planar Transistor

for power switching and electron rectifier applications.

The transistor is subdivided into one group according to its DC current gain.



1.Base 2.Collector 3.Emitter

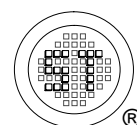
TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	600	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	9	V
Collector Current	I_C	1.5	A
Power Dissipation	P_{tot}	1.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_{amb} = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 100\text{ mA}$	h_{FE}	10	70	-
Collector Base Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CBO}$	600	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	400	-	V
Emitter Base Breakdown Voltage at $I_E = 1\text{ mA}$	$V_{(BR)EBO}$	9	-	V
Collector Cutoff Current at $V_{CB} = 600\text{ V}$	I_{CBO}	-	100	nA
Emitter Cutoff Current at $V_{EB} = 9\text{ V}$	I_{EBO}	-	100	μA
Collector Emitter Saturation Voltage at $I_C = 1\text{ A}$, $I_B = 250\text{ mA}$	$V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage at $I_C = 1\text{ A}$, $I_B = 250\text{ mA}$	$V_{BE(sat)}$	-	1.2	V



Dated : 22/03/2006



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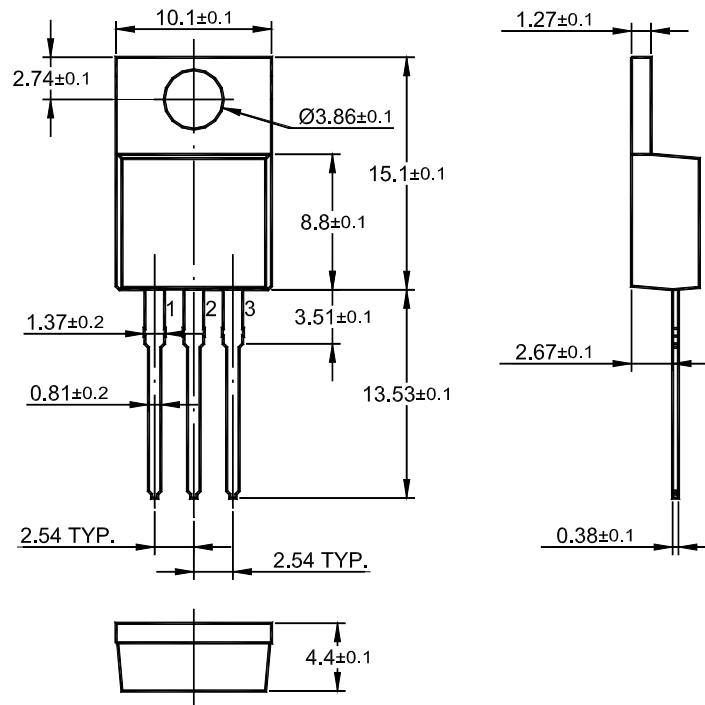
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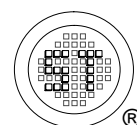
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TO-220 PACKAGE OUTLINE



Dimensions in mm



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